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| **FQP30N06L N-channel** | **FQP27P06**   **P-channel** | **IRL2203N** **N-channel** | **IRLZ44N N-channel** |
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| **Enhancement Mode MOSFET** | **Enhancement Mode Power MOSFET** | **HEXFET® Power MOSFET** | **HEXFET® Power MOSFET** |
| VDSS = **60 V** VGSS = **±20 V**  ID at 25°C = **32 A** CISS = **800 pF typ.**  RDS(on) at 5 V and 16 A = **0.045 Ω max.**  VGS(th) = **1 V min. / 2.5 V max.**  PD (Tc = 25°C) = **79 W — 0.53 W/°C**  TJ, TSTG = **-55 to 175 °C** | VDSS = **-60 V** VGSS = **±25 V**  ID at 25°C = **-27 A** CISS = **1100 pF typ.**  RDS(on) at -10 V and -13.5 A = **0.07 Ω max.**  VGS(th) = **-2 V min. / -4 V max.**  PD (Tc = 25°C) = **120 W — 0.8 W/°C**  TJ, TSTG = **-55 to 175 °C** | VDSS = **30 V** VGS = **±16 V**  ID at 25°C = **116 A** CISS = **3290 pF typ.**  RDS(on) at 10 V and 60 A = **0.007 Ω max.**  VGS(th) = **1 V min.**  PD (Tc = 25°C) = **180 W — 1.2 W/°C**  TJ, TSTG = **-55 to 175 °C** | VDSS = **55 V** VGS = **±16 V**  ID at 25°C = **47 A** CISS = **3290 pF typ.**  RDS(on) at 5 V and 25 A = **0.025 Ω max.**  VGS(th) = **1 V min. / 2 V max.**  PD (Tc = 25°C) = **110 W — 0.71 W/°C**  TJ, TSTG = **-55 to 175 °C** |
| **NDP6020P P-channel** | **PSMN022**  **N-channel** | **BS170**   **N-channel** | **HUF76423P3 N-channel** |
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| **Logic Level Enhancement M. MOSFET** | **Logic Level MOSFET** | **Small Signal MOSFET** | **Logic Level UltraFET Power MOSFET** |
| VDSS = **-20 V** VGSS = **±8 V**  ID cont. = **-24 A max.** CISS = **1100 pF typ.**  RDS(on) at -4.5 V and -12 A = **0.05 Ω max.**  VGS(th) = **-0.4 V min. / -1 V max.**  PD (Tc = 25°C) = **60 W — 0.4 W/°C**  **TJ, TSTG = -65 to 175 °C** | VDSS = **30 V** VGS = **±20 V**  ID at 25°C = **30 A** CISS = **3290 pF typ.**  RDS(on) at 4.5 V and 5 A = **0.034 Ω max.**  VGS(th) = **1.3 V min. / 2.1 max.**  Ptot (Tmb = 25°C) = **41 W**  **TJ, TSTG = -55 to 175 °C** | VDS(BR) = **90 V typ.** VGS = **±20 V**  ID = **0.5 A** CISS = **60 pF max.**  RDS(on) at 10 V and 0.2 A = **5 Ω max.**  VGS(th) = **0.8 V min. / 3 V max.**  PD (Tc = 25°C) = **0.35 W**  TJ, TSTG = **-55 to 150 °C** | VDSS = **60 V** VGS = **±16 V**  ID at 25°C= **33 A** CISS = **60 pF max.**  RDS(on) at 5 V and 23 A = **0.035 Ω max.**  VGS(th) = **1 V min. / 3 V max.**  PD (Tc = 25°C) = **85 W — 0.567 W/°C**  TJ, TSTG = **-55 to 175 °C** |
| **IPP80N03S4L-03 N-channel** | **SPP15P10PL H P-channel** | **VN0300L-G N-channel** | **VP0808L-G P-channel** |
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| **OptiMOS® - T2 Power MOSFET** | **SIPMOS® Power MOSFET** | **Enhancement Mode MOSFET** | **Enhancement Mode MOSFET** |
| V(BR)DSS = **30 V** VGS = **±16 V**  ID at 25°C = **80 A** CISS = **7500 pF typ.**  RDS(on) at 4.5 V and 40 A = **2.8 Ω typ.**  VGS(th) = **1 V min. / 2.2 V max.**  Ptot (Tc = 25°C) = **136 W**  TJ, TSTG = **-55 to 175 °C** | V(BR)DSS = **-100 V** VGS = **±20 V**  ID at 25°C = **-15 A** CISS = **1120 pF typ.**  RDS(on) at -4.5 V and -9.7 A = **0.270 Ω max.**  VGS(th) = **-1 V min. / -2 V max.**  Ptot (Tc = 25°C) = **128 W**  TJ, TSTG = **-55 to 175 °C** | BVDSS = **30 V** VGS = **±30 V**  ID = **640 mA** CISS = **190 pF typ.**  RDS(on) at 5 V and 300 mA = **3.3 Ω max.**  VGS(th) = **0.8 V min. / 2.5 V max.**  PD (Tc = 25°C) = **1 W**  TJ, TSTG = **-55 to 150 °C** | BVDSS = **-80 V** VGS = **±30 V**  ID = **-280 mA** CISS = **150 pF max.**  RDS(on) at -10 V and -1 A = **5 Ω max.**  VGS(th) = **-1 V min. / -4.5 V max.**  PD (Tc = 25°C) = **1 W**  TJ, TSTG = **-55 to 150 °C** |
| **SFT1342-W P-channel** | **2N7000 N-channel** | **NTA4151PT1G P-channel** |  |
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| **Power MOSFET w/ESD-Protected Gate** | **Enhancement Mode MOSFET** | **Small Signal MOSFET w/Gate Zener** |  |
| VDSS = **-60 V** VGSS = **±20 V**  ID at 25°C = **-12 A** CISS = **1150 pF typ.**  RDS(on) at -4.5 V and -6 A = **0.062 Ω typ.**  VGS(th) = **-1.2 V min. / -2.6 V max.**  PD (Tc = 25°C) = **15 W**  TSTG = **-55 to 150 °C** | VDSS = **60 V** VGSS = **±20 V**  ID = **200 mA** CISS = **20 pF typ.**  RDS(on) at 4.5 V and 75 mA = **1.8 Ω typ.**  VGS(th) = **0.8 V min. / 3 V max.**  PD (derated above 25°C) = **400 mW**  TJ, TSTG = **-55 to 150 °C** | VDSS = **-20 V** VGS = **±6 V**  ID = **-760 mA** CISS = **156 pF**  RDS(on) at -4.5 V and 350 mA = **0.26 Ω typ.**  VGS(th) = **-0.45 V min. / -1.2 V max.**  PD (TJ at 25°C) = **301 mW**  TJ, TSTG = **-55 to 150 °C** |  |
| **PN4117 N-channel** |  |  |  |
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| **Ultra High Input Impedance JFET** |  |  |  |
| BVDSS = **-40 V** V(BR)GSS = **-40 V**  IDSS = **30 mA** CISS = **3 pF max.**  GFS(on) at 10 V, f = 1 kHz = **210 µS max.**  VGS(off) = **-1.8 V max.**  PD (TA at 25°C) = **300 mW**  TJ = **-55 to 125 °C** |  |  |  |